- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

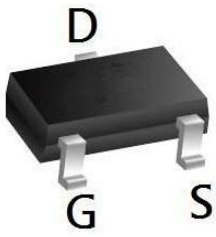
BVDSS	RDSON	ID
-30V	20mΩ	-9.0A

Description

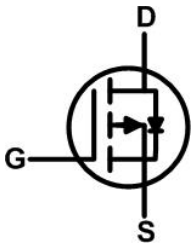
The ZX 30P09 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

TheZX 30P09 meet the RoHS and Green Product requirement

SOT23-3L Pin Configuration



pin assignment



Schematic diagram

Package Marking and Ordering Information

Product	Package	Marking	Packing	Min Unit Quantity
ZX 30P09	SOT23-3L	*	3000PCS/Reel	3000PCS

Absolute Maximum Ratings (T_A=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_A= 25℃	-9	A
		T_A= 100℃	-5.0	A
I_{DM}	Pulsed Drain Current note1		-36	A
E_{AS}	Single Pulsed Avalanche Energy note2		25	mJ
P_D	Power Dissipation	T_A= 25℃	3.0	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		48	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D= -250μA	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -30V, V_{GS} = 0V,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS} =0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D= -250μA	-1.0	-1.5	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance Note3	V_{GS} =-10V, I_D =-9A	-	20	25	mΩ
		V_{GS} =-4.5V, I_D =-5A	-	27	38	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = -15V, V_{GS} = 0V, f = 1.0MHz	-	900	-	pF
C_{oss}	Output Capacitance		-	125	-	pF
C_{rss}	Reverse Transfer Capacitance		-	109	-	pF
Q_g	Total Gate Charge	V_{DS}= -15V, I_D = -8A, V_{GS} = -10V	-	42	-	nC
Q_{gs}	Gate-Source Charge		-	8.8	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	7.3	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = -15V, I_D = -1A, V_{GS}=-10V, R_{GEN}=6Ω	-	13	-	ns
t_r	Turn-on Rise Time		-	15	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	198	-	ns
t_f	Turn-off Fall Time		-	98	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-9	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-36	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = -9A	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25℃, V_{DD}=-15V, V_G=-10V, R_G=25Ω, L=0.5mH, I_{AS}=-10A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

Figure1: Output Characteristics

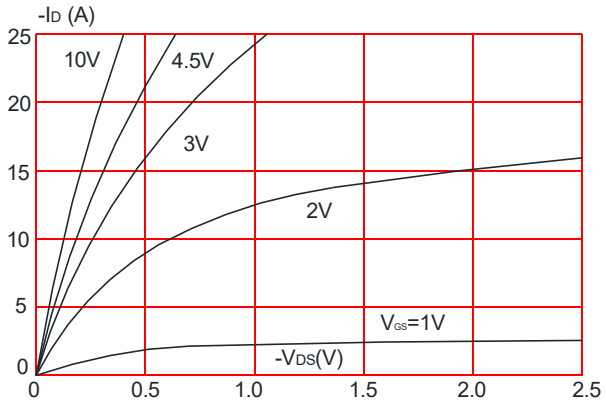


Figure 2: Typical Transfer Characteristics

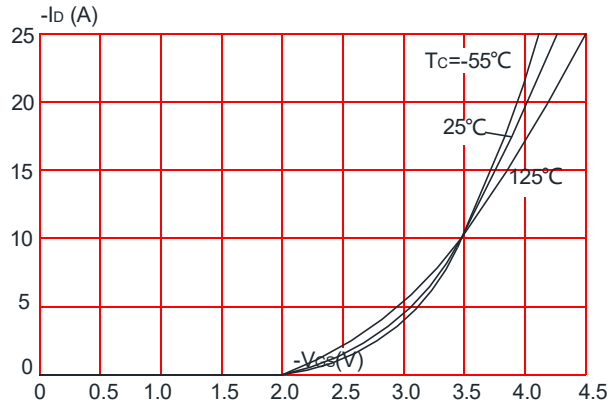


Figure 3: On-resistance vs. Drain Current

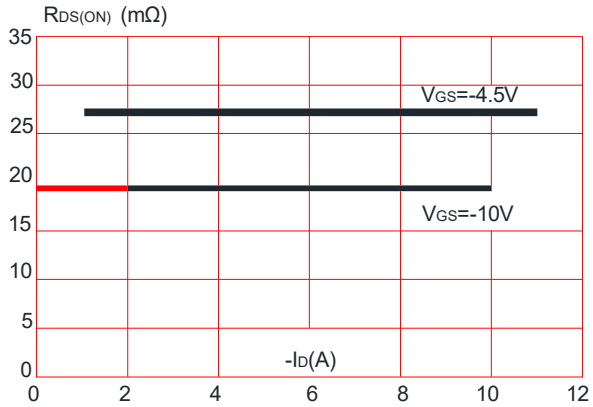


Figure 4: Body Diode Characteristics

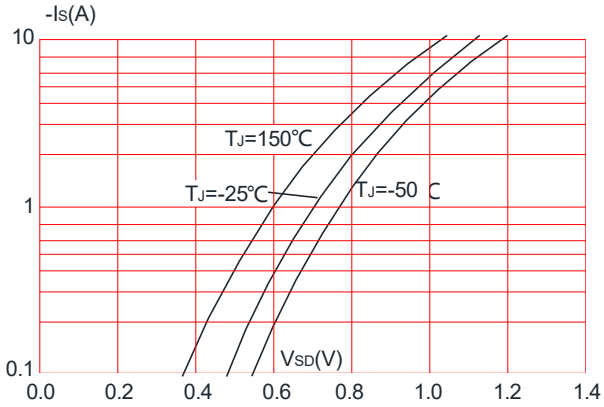


Figure 5: Gate Charge Characteristics

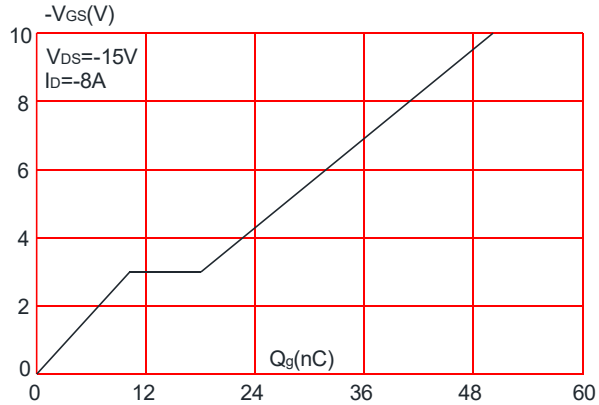


Figure 6: Capacitance Characteristics

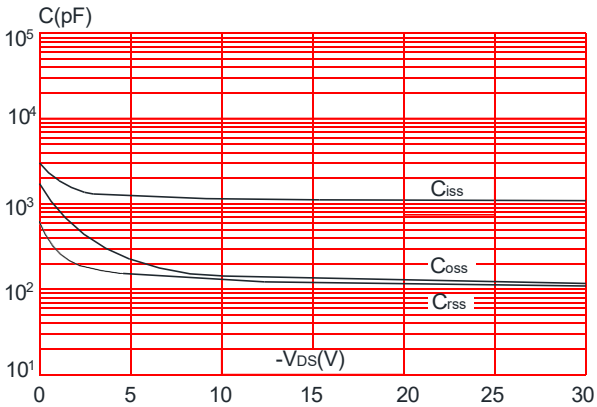


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

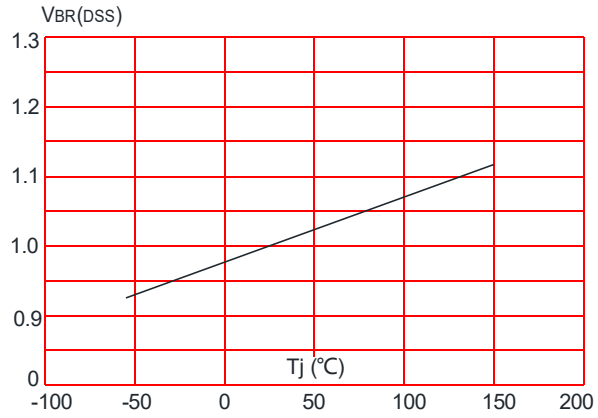


Figure 8: Normalized on Resistance vs. Junction Temperature

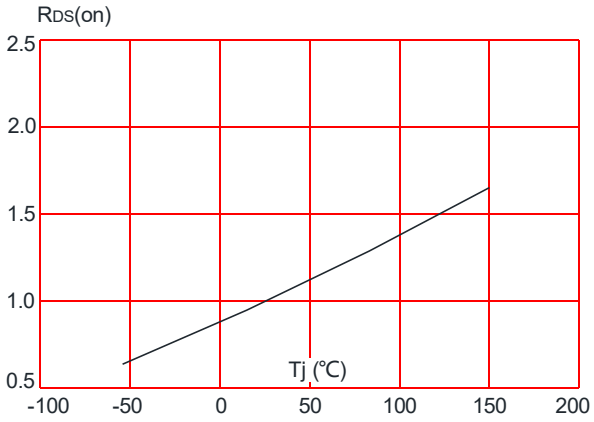


Figure 9: Maximum Safe Operating Area

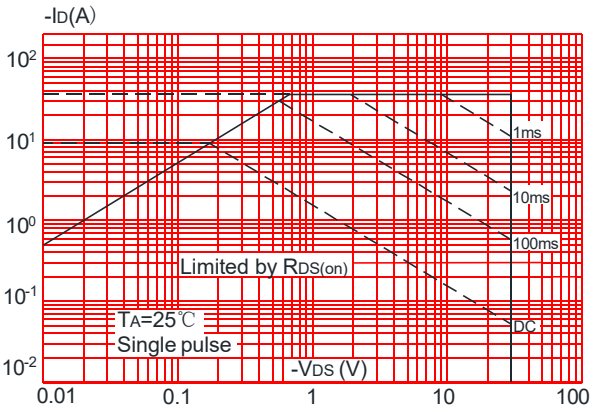


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

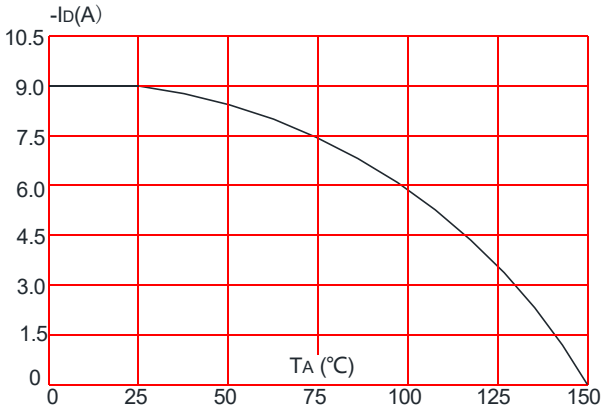
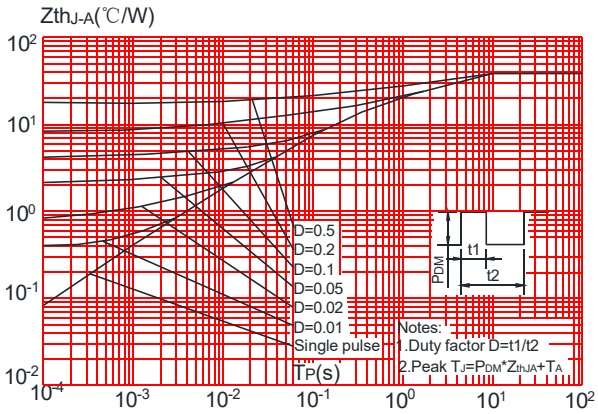


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Test Circuit

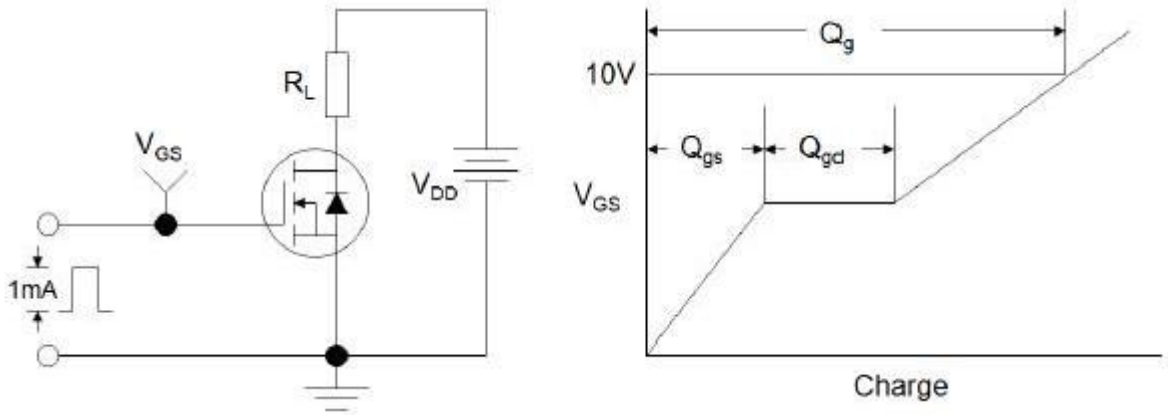


Figure1:Gate Charge Test Circuit & Waveform

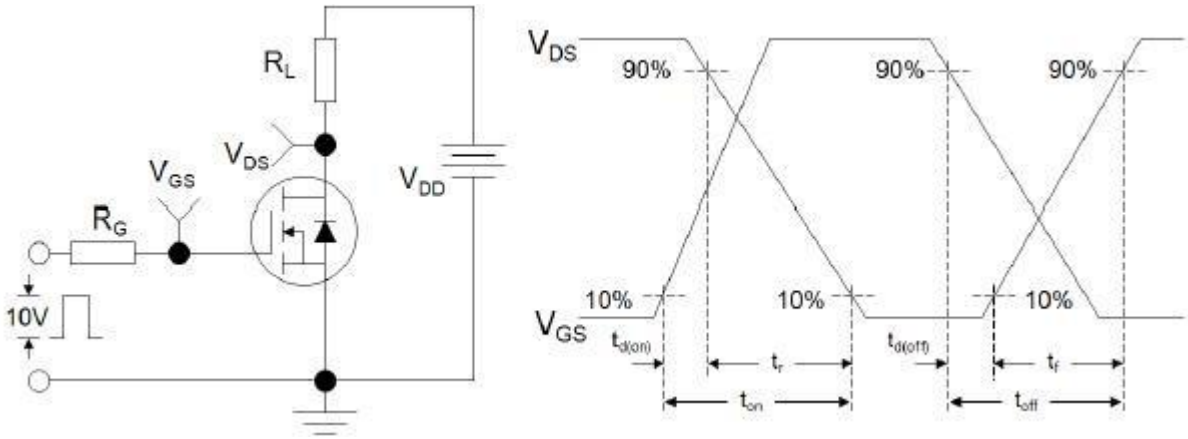


Figure 2: Resistive Switching Test Circuit & Waveforms

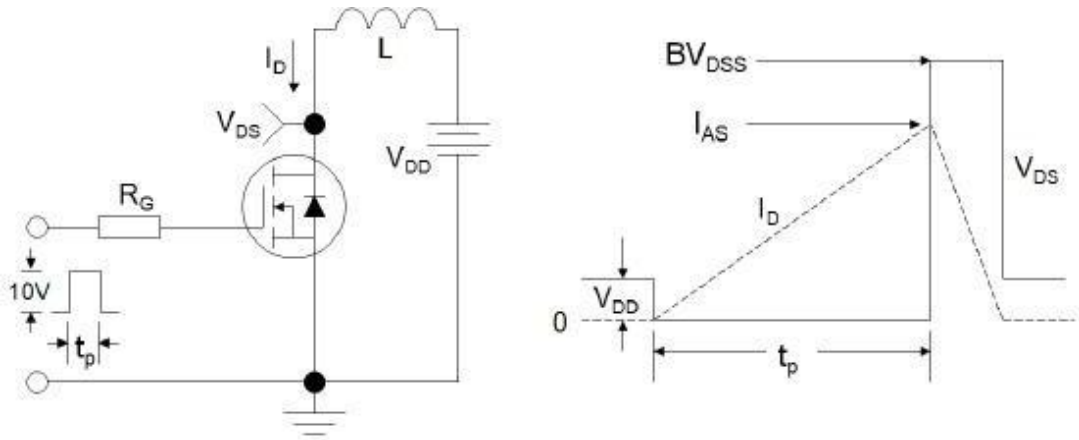
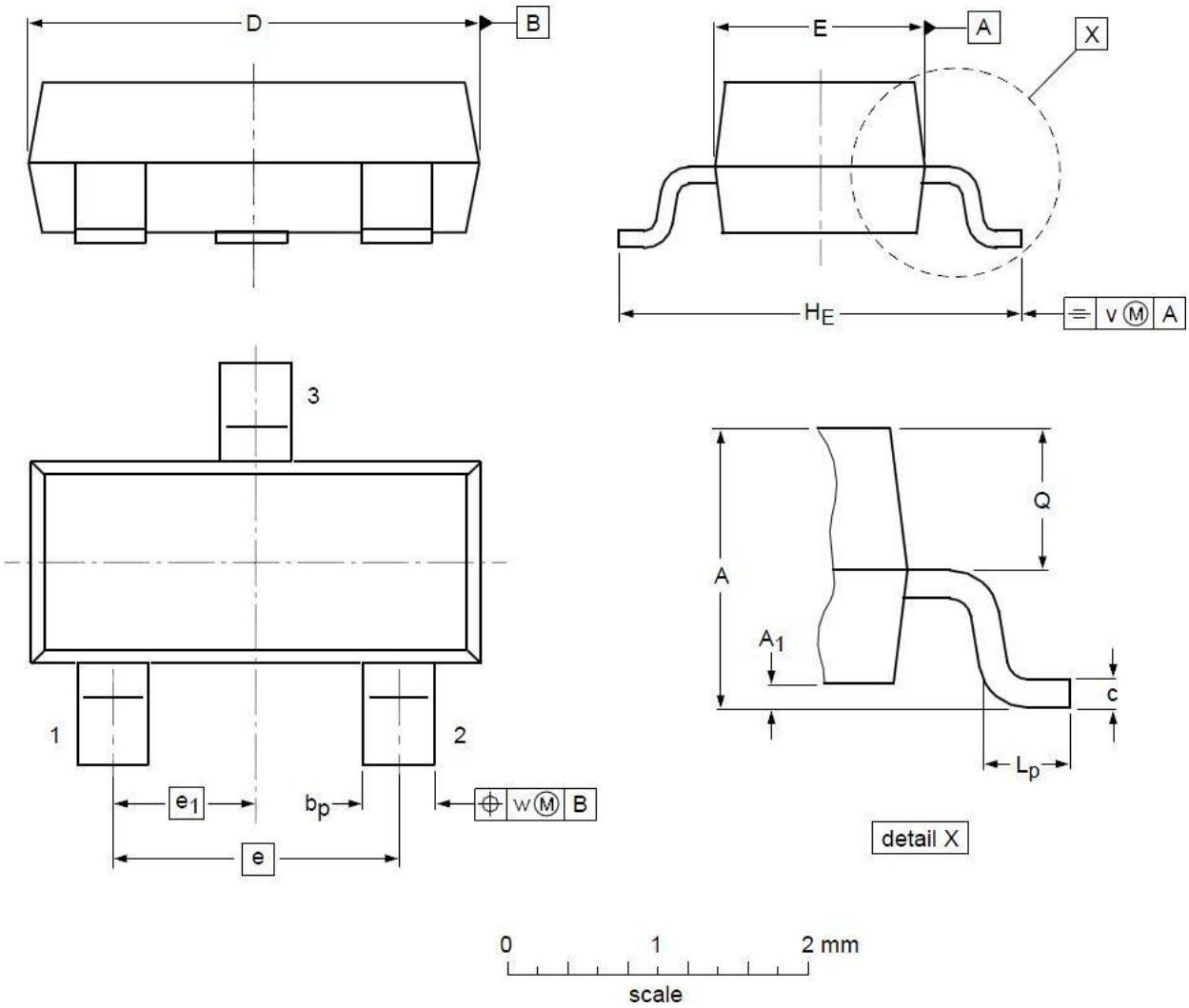


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Package Mechanical Data-SOT-23-3L



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.01	1.15	**A_1**	0.01	0.05	0.10
b_p	0.30	0.42	0.50	**c**	0.08	0.13	0.15
D	2.80	2.92	3.00	**E**	1.20	1.33	1.40
e	--	1.90	--	**e_1**	--	0.95	--
H_E	2.25	2.40	2.55	**L_p**	0.30	0.42	0.50
Q	0.45	0.49	0.55	**v**	--	0.20	--
w	--	0.10	--				